



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Arndt  
RECEIVED  
PATENT  
500.34397CV  
TECHNOLOGY CENTER 2800  
JUL 3 2002  
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Applicants: MIURA, et al

Serial No.: Serial No.09/977,207

Filed: October 16, 2001

For: SEMICONDUCTOR DEVICE AND PRODUCTION THEREOF

Group of Parent: 2823

Examiner of Parent: T. Dang

AMENDMENT

Commissioner of Patents  
Washington, D.C. 20231

July 1, 2002

Sir:

In response to the Office Action of March 1, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel Claims 12 - 14 without prejudice or disclaimer.

Please amend Claims 15 and 17 as follows:

15. (Amended) A process for producing a semiconductor device which comprises forming an element-separating oxide film on a silicon substrate by thermal oxidation, and thereafter carrying out a heat-treatment at a temperature of not lower than 800°C while keeping a surface of the oxide film in an inert atmosphere, followed by formation of a gate oxide film,